

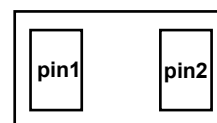
Desicription

- ◆ This low-power TVS (Transient Voltage Suppressor) is mainly used for signal and power supply to protect the back-stage circuit from ESD(Electrostatic Discharge) and EFT(Electrical Fast Transients) and improve the reliability of the product, because its extremely small package is suitable for various portable devices and mobile electronic devices.



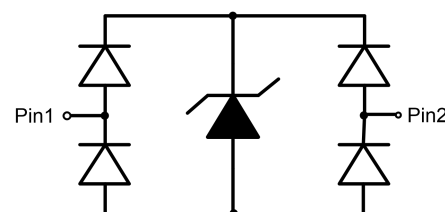
Features

- ◆ IEC61000-4-2(ESD): $\pm 30\text{KV}$ Max Air
 $\pm 30\text{KV}$ Max Contact
- ◆ IEC61000-4-4(EFT): $40\text{A}(5/50\text{ns})$
- ◆ IEC61000-4-5(Surge): $7.0\text{A}(8/20\mu\text{s})$
- ◆ Line capacitance: $0.40\text{pF}(\text{typical})@1\text{MHz}$
- ◆ Very low reverse current: $I_R < 0.1\mu\text{A}(\text{typical})$
- ◆ Halogen free ,Lead free and RoHs



Application

- ◆ Cellular phones
- ◆ Portable devices
- ◆ Digital cameras
- ◆ Player
- ◆ Smart home
- ◆ Robot



Circuit Diagram

Order information

Model	Marking	Package	shipping
ESD3V3D004SA	f	DFN1006-2L	10000/Tape&Reel

Electrical characteristic(T=25°C, unless otherwise specified)

Parameter	Symbol	Conditions	Min.	TYP.	Max.	Units
Reverse stand-off voltage	V_{RWM}				± 3.3	V
Reverse leakage current	I_R	$V_{RWM}=3.3V$			0.1	μA
Reveres breakdown voltage	V_B	$I_T=1\mu A$	3.7			V
Reveres holding voltage	V_h	$I_h=100mA$	3.3		6.0	V
Dynamic resistance	R_{DYN}	$T_p=10/100ns$		0.25		Ω
Clamping voltage	V_C	$I_{PP}=16A, t_p=10/100ns$		8.5		V
		$I_{PP}=7 A, t_p=8/20\mu s$		8.0		V
Junction capacitance	C_J	$V_R=0V f=1MHz$		0.4	0.5	pF
		$V_R=0V f=1GHz$		0.3		pF

Electrical characteristic(T=25°C, unless otherwise specified)

V_{RWM} Reverse stand-offvoltage

I_R Reverse leakage current

V_{CL} Clamping voltage

I_{PP} Peak pulse current

V_{TRIG} Reverse trigger voltage

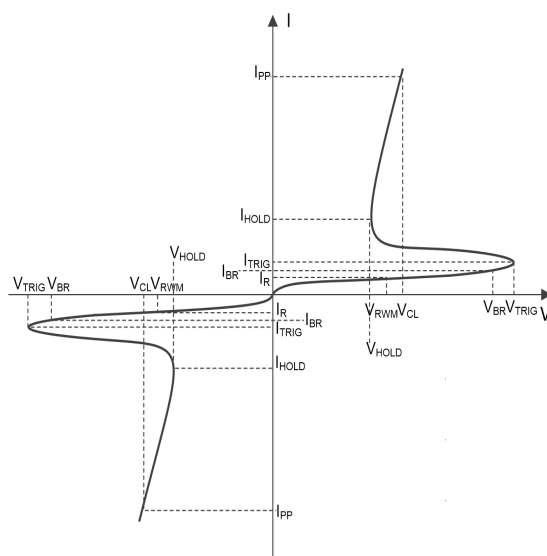
I_{TRIG} Reverse trigger current

V_{BR} Reverse breakdown voltage

I_{BR} Reverse breakdown current

V_{HOLD} Reverse holding voltage

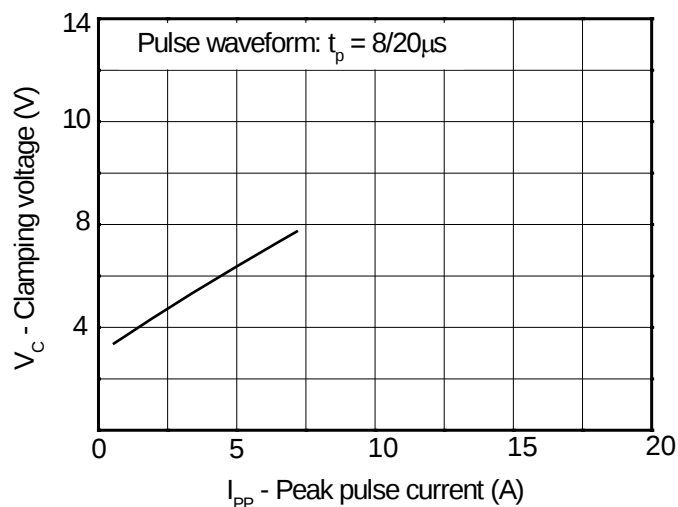
I_{HOLD} Reverse holding current



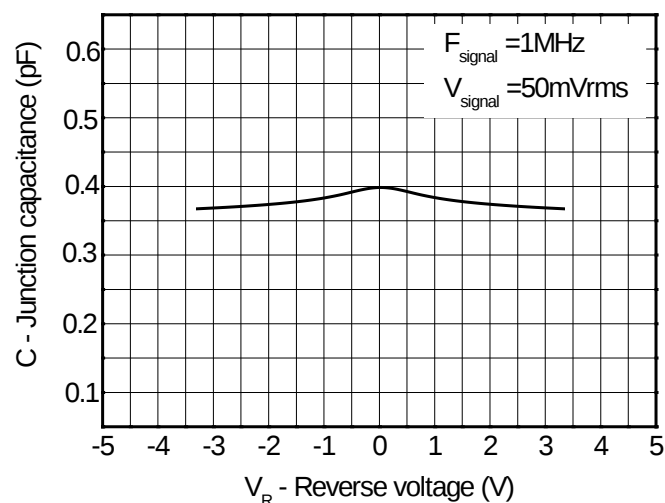
Maximum Rating

Rating	symbol	value	Units
Peak Pulse Current($t_p=8/20\mu s$)	I_{pp}	7.0	A
ESD per IEC61000-4-2(Contact)	V_{ESD}	± 30	KV
ESD per IEC61000-4-2(Air)		± 30	
Operating Temperature	T_J	-40~125	$^{\circ}C$
Storage Temperature	T_{STG}	-55~155	$^{\circ}C$

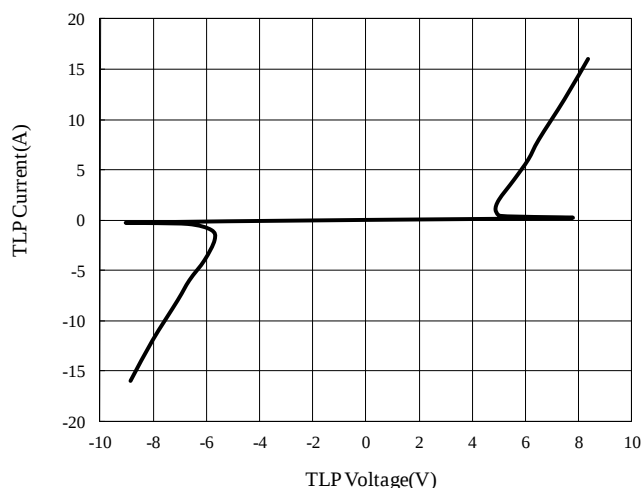
Typical characteristic



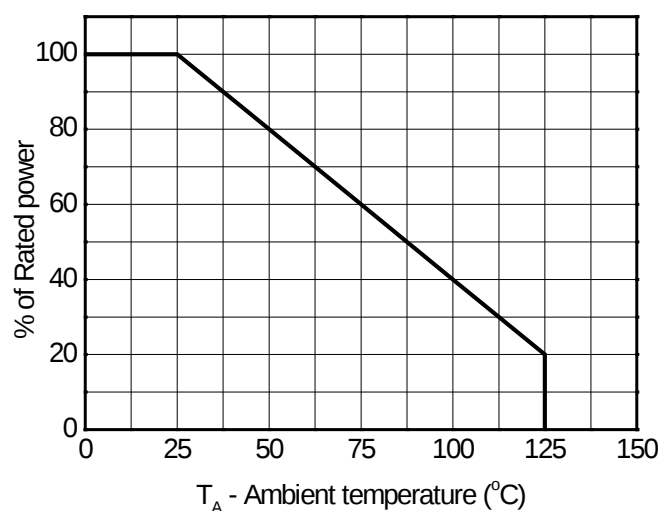
Clamping voltage vs. Peak pulse current



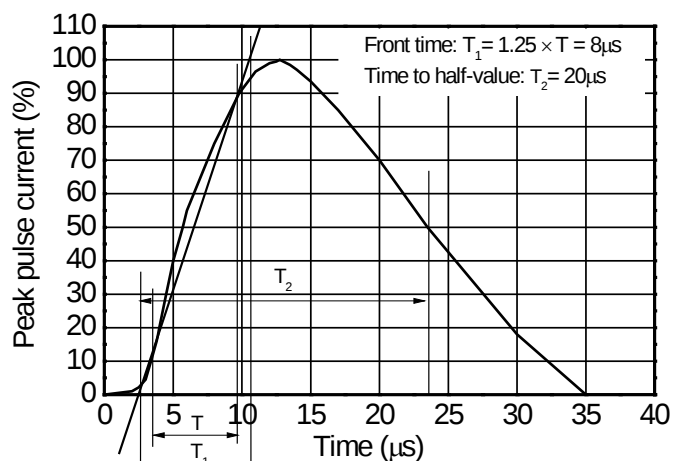
Capacitance vs. Reverse voltage



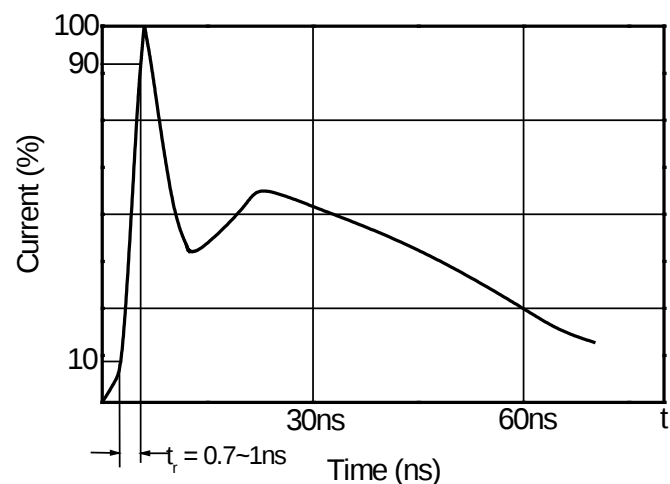
TLP Testing of I/O to I/O



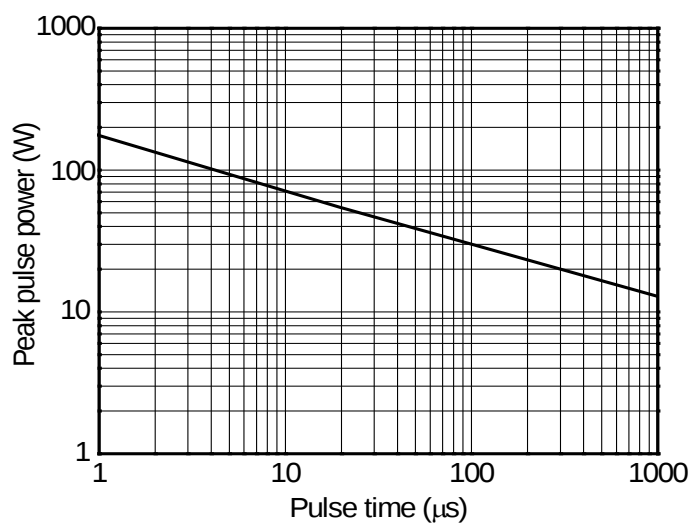
Power derating vs. Ambient temperature



8/20 μs waveform per IEC61000-4-5

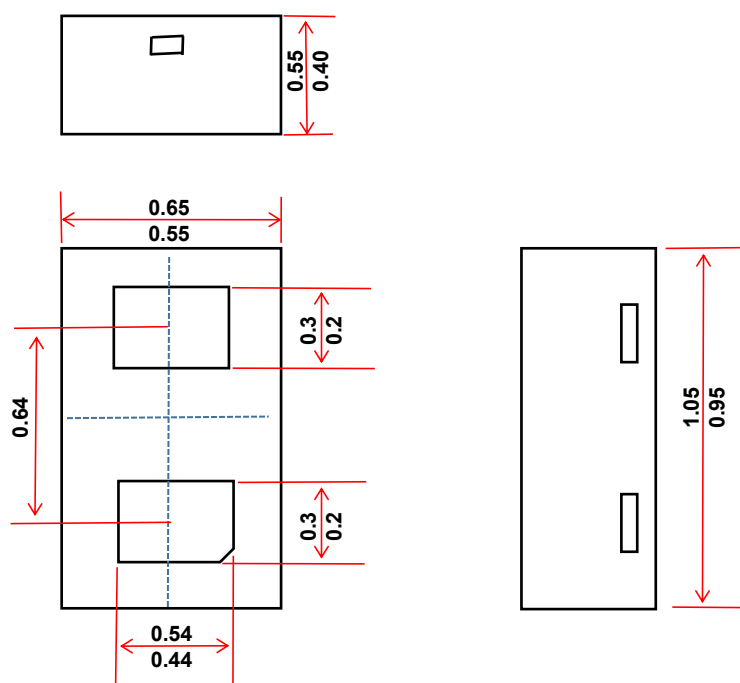


Contact discharge current waveform per IEC61000-4-2



Non-repetitive peak pulse power vs. Pulse time

Dimension outline Unit:mm

DFN1006-2L(SOD882)

Recommended Mounting Pad Layout Unit:mm
